Discrete POWER & Signal **Technologies** 

# MPS6531

FAIRCHILD SEMICONDUCTOR TM

## **MPS6531**



## NPN General Purpose Amplifier

This device is designed for use as a medium power amplifier and switch requiring collector currents to 500 mA. Sourced from Process 19. See PN2222A for characteristics.

#### **Absolute Maximum Ratings\*** TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
$V_{CEO}$	Collector-Emitter Voltage	40	V
V <sub>CBO</sub>	Collector-Base Voltage	60	V
$V_{\text{EBO}}$	Emitter-Base Voltage	5.0	V
I <sub>C</sub>	Collector Current - Continuous	1.0	A
T <sub>J</sub> , T <sub>stg</sub>	Operating and Storage Junction Temperature Range	-55 to +150	°C

\*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

### NOTES:

1) These ratings are based on a maximum junction temperature of 150 degrees C.
2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

### **Thermal Characterist**

ICS	TA = 25°C unless otherwise noted

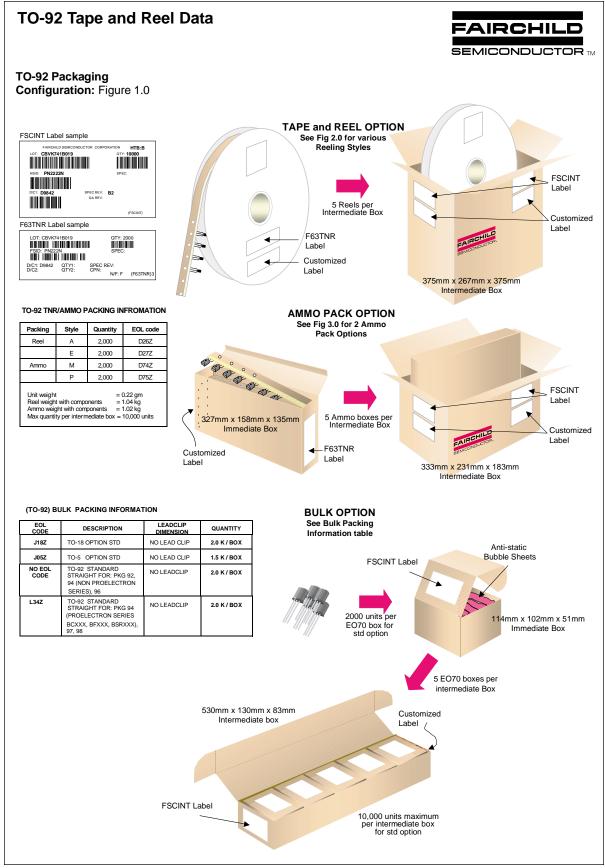
Symbol	Characteristic	Max	Units
		MPS6531	
P <sub>D</sub>	Total Device Dissipation Derate above 25℃	625 5.0	mW mW/°C
$R_{\theta JC}$	Thermal Resistance, Junction to Case	83.3	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	200	°C/W

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# NPN General Purpose Amplifier (continued)

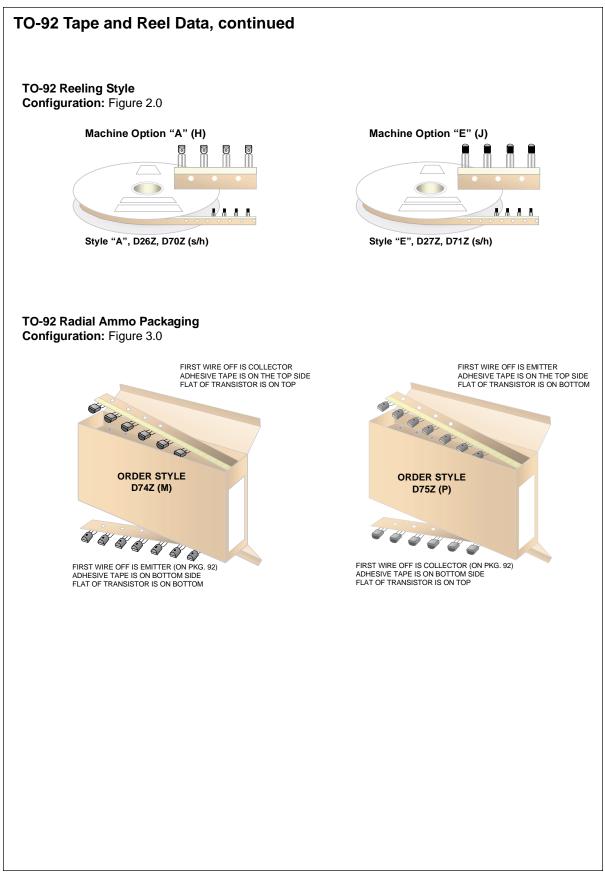
**MPS6531** 

Symbol	Parameter	Test Conditions	Min	Max	Units
	RACTERISTICS	1			•
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage*	$I_{\rm C} = 10 \text{ mA}, I_{\rm B} = 0$	40		V
V <sub>(BR)CBO</sub>	Collector-Base Breakdown Voltage	$I_{\rm C} = 10 \ \mu {\rm A}, \ I_{\rm E} = 0$	60		V
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	$I_{\rm E} = 10 \mu {\rm A},  I_{\rm C} = 0$	5.0		V
СВО	Collector Cutoff Current			50 2.0	nA μA
	ACTERISTICS*				
	DC Current Gain	$V_{CE} = 1.0 \text{ V}, I_{C} = 10 \text{ mA}$	60		
ΨE		$V_{CE} = 1.0 \text{ V}, I_{C} = 100 \text{ mA}$	90	270	
		$V_{CE} = 10 \text{ V}, I_C = 500 \text{ mA}$	50		
	Collector-Emitter Saturation Voltage	$I_{\rm C} = 100 \text{ mA}, I_{\rm B} = 10 \text{ mA}$		0.3	V
	_			1.0	
V <sub>BE(Sat)</sub> SMALL S C <sub>ob</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 100 mA, I <sub>B</sub> = 10 mA V <sub>CB</sub> = 10 V, f = 100 kHz		1.0 5.0	V pF
V <sub>BE(Sat)</sub> SMALL S C <sub>ob</sub>	Base-Emitter Saturation Voltage	$I_{\rm C}$ = 100 mA, $I_{\rm B}$ = 10 mA			
C <sub>ob</sub>	Base-Emitter Saturation Voltage	$I_{\rm C}$ = 100 mA, $I_{\rm B}$ = 10 mA			
V <sub>BE(Sat)</sub> SMALL S C <sub>ob</sub>	Base-Emitter Saturation Voltage	$I_{\rm C}$ = 100 mA, $I_{\rm B}$ = 10 mA			
V <sub>BE(Sat)</sub> SMALL S C <sub>ob</sub>	Base-Emitter Saturation Voltage	$I_{\rm C}$ = 100 mA, $I_{\rm B}$ = 10 mA			
V <sub>BE(Sat)</sub> SMALL S C <sub>ob</sub>	Base-Emitter Saturation Voltage	$I_{\rm C}$ = 100 mA, $I_{\rm B}$ = 10 mA			
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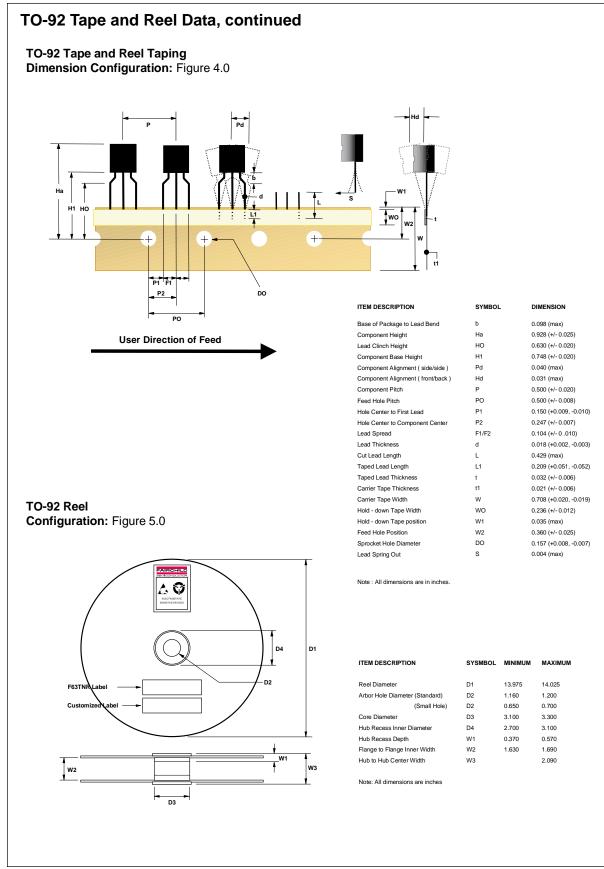


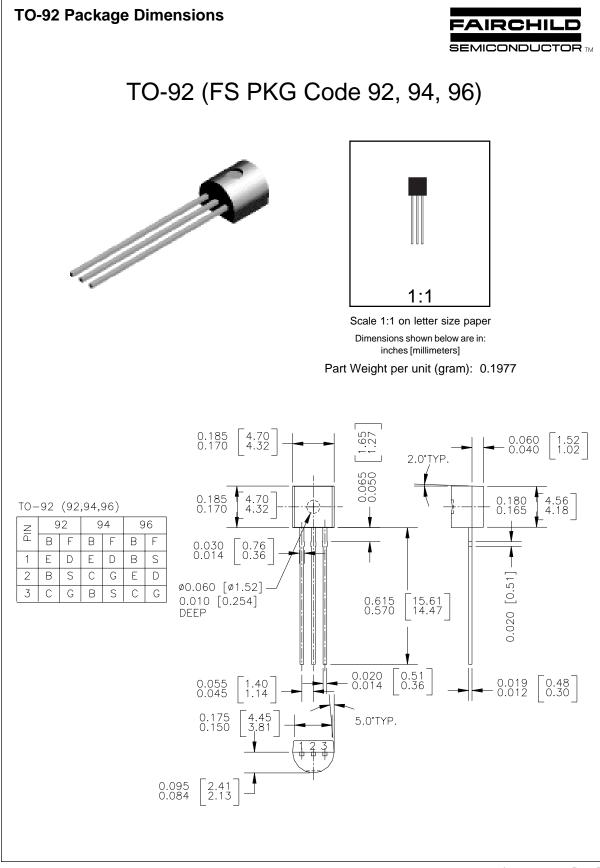
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